CORRECTION

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Correction: Integration of BiFeO₃/La_{0.7}Sr_{0.3}MnO₃ heterostructures with III–V semiconductors for low-power non-volatile memory and multiferroic field effect transistors

Md. Shafiqur Rahman,^{*a} Susmita Ghose,^a Liang Hong,^b Pradip Dhungana,^c Abbas Fahami,^a Javad R. Gatabi,^a Juan S. Rojas-Ramirez,^d Alex Zakhidov,^{ac} Robert F. Klie,^b R. K. Pandey^d and Ravi Droopad^d

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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^a Material Science, Engineering and Commercialization, Texas State University, San Marcos, TX 78666, USA. E-mail: m_r424@txstate.edu

^b Department of Physics, University of Illinois at Chicago, Chicago, IL 60607, USA

^c Department of Physics, Texas State University, San Marcos, TX 78666, USA

^d Ingram School of Engineering, Texas State University, San Marcos, TX 78666, USA